L Number	Hits	Search Text	DB	Time stamp
1	65	STI and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory	USPAT; US-PGPUB	2004/02/21 10:03
2	65	(STI and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory) and @ad<20030820	USPAT; US-PGPUB	2004/02/21 10:11
3	0	STI and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory	EPO; JPO; DERWENT; IBM_TDB	2004/02/21 10:00
4	5	((STI and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory) and @ad<20030820) and diode	USPAT; US-PGPUB	2004/02/21 10:03
5	5	STI and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode	USPAT; US-PGPUB	2004/02/21 10:04
6	5	(isolation with trench) and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode	USPAT; US-PGPUB	2004/02/21 10:04
7	24	(isolation with trench) and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode	USPAT; US-PGPUB	2004/02/21 10:33
8	19	((isolation with trench) and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode) not ((isolation with trench) and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode)	USPAT; US-PGPUB	2004/02/21 10:05
9	19	(((isolation with trench) and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode) not ((isolation with trench) and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode)) and @ad<20030820	USPAT; US-PGPUB	2004/02/21 10:34
10	200	(STI or (isolation near3 trench)) and (interlayer with dielectric) and (doping or implantation or implanting) and memory and bit and word	USPAT; US-PGPUB	2004/02/21 11:10
11	200	((STI or (isolation near3 trench)) and (interlayer with dielectric) and (doping or implantation or implanting) and memory and bit and word) and @ad<20030820	USPAT; US-PGPUB	2004/02/21 10:34
12	150	(((STI or (isolation near3 trench)) and (interlayer with dielectric) and (doping or implantation or implanting) and memory and bit and word) and @ad<20030820) not ((STI and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory) and @ad<20030820)	USPAT; US-PGPUB	2004/02/21 10:34

13	132	(((((STI or (isolation near3 trench)) and (interlayer with dielectric) and (doping or implantation or implanting) and memory and bit and word) and @ad<20030820) not ((STI and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory) and @ad<20030820)) not (((isolation with trench) and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode) not ((isolation with trench) and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode))	USPAT; US-PGPUB	2004/02/21 10:34
14	62	((((((STI or (isolation near3 trench)) and (interlayer with dielectric) and (doping or implantation or implanting) and memory and bit and word) and @ad<20030820) not ((STI and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory) and @ad<20030820)) not (((isolation with trench) and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode) not ((isolation with trench) and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode))) and plug	USPAT; US-PGPUB	2004/02/21 11:08
15	70	((((((STI or (isolation near3 trench)) and (interlayer with dielectric) and (doping or implantation or implanting) and memory and bit and word) and @ad<20030820) not ((STI and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory) and @ad<20030820)) not (((isolation with trench) and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode) not ((isolation with trench) and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode))) not (((((STI or (isolation near3 trench)) and (interlayer with dielectric) and (doping or implantation or implanting) and memory and bit and word) and @ad<20030820) not ((STI and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory) and @ad<20030820)) not (((isolation with trench) and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode) not ((isolation with trench) and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode))) and plug)	USPAT; US-PGPUB	2004/02/21 10:53

| 16 | 31 | (((((((STI or (isolation near3 trench)) and (interlayer with dielectric) and (doping or implantation or implanting) and memory and bit and word) and @ad<20030820) not ((STI and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory) and @ad<20030820)) not (((isolation with trench) and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode) not ((isolation with trench) and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode))) not ((((((STI or (isolation near3 trench)) and (interlayer with dielectric) and (doping or implantation or implanting) and memory and bit and word) and @ad<20030820) not ((STI and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory) and @ad<20030820)) not (((isolation with trench) and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode) not ((isolation with trench) and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode))) and plug)) and buried | USPAT; US-PGPUB | 2004/02/21 10:54 |

| 17 | 39 | (((((STI or (isolation near3 trench)) and (interlayer with dielectric) and (doping or implantation or implanting) and memory and bit and word) and @ad<20030820) not ((STI and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory) and @ad<20030820)) not (((isolation with trench) and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode) not ((isolation with trench) and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode))) not ((((((STI or (isolation near3 trench)) and (interlayer with dielectric) and (doping or implantation or implanting) and memory and bit and word) and @ad<20030820) not ((STI and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory) and @ad<20030820)) not (((isolation with trench) and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode) not ((isolation with trench) and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode))) and plug)) not (((((((STI or (isolation near3 trench)) and (interlayer with dielectric) and (doping or implantation or implanting) and memory and bit and word) and @ad<20030820) not ((STI and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory) and @ad<20030820)) not (((isolation with trench) and (interlayer with dielectric) and plug and (doping or implantation ·or implanting) and memory and diode) not ((isolation with trench) and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode))) not ((((((STI or (isolation near3 trench)) and (interlayer with dielectric) and (doping or implantation or implanting) and memory and bit and word) and @ad<20030820) not ((STI and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory) and @ad<20030820)) not (((isolation with trench) and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode) not ((isolation with trench) and buried and (interlayer with dielectric) and plug and (doping or implantation or implanting) and memory and diode))) and plug)) and buried) | USPAT; US-PGPUB | 2004/02/21 11:08 |
| 18 | 0 | (STI or (isolation near3 trench)) and (interlayer with dielectric) and (doping or implantation or implanting) and memory and bit and word | EPO; JPO; DERWENT; IBM_TDB | 2004/02/21 11:10 |